

L Number	Hits	Search Text	DB	Time stamp
-	74	chau-robert-s.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:50
-	2	barlage-douglas.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:51
-	7	jin-been-yih.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:51
-	79	chau-robert-s.in. barlage-douglas.in. jin-been-yih.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:51
-	3	(chau-robert-s.in. barlage-douglas.in. jin-been-yih.in.) and ("SOI" adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:54
-	0	("SOI" adj transistor) and (low adj bandgap adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 10:55
-	1	("SOI" adj transistor) and (narrow adj bandgap adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:36
-	20	("SOI" adj transistor) and bandgap	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:36
-	20	((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:37
-	18	((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4)) and source and drain	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:37
-	18	((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4)) and source and drain) and channel	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:48
-	1	(((((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4)) and source and drain) and channel) and ((narrow or low) adj (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:57
-	607	(channel and (narrow or low) adj (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:37
-	23	((channel and (narrow or low) adj (bandgap or (band adj gap)))) and (("InSb" or "InAs" or "PbTe") and (("SOI" or insulat\$\$) adj substrate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:59
-	22	((channel and (narrow or low) adj (bandgap or (band adj gap)))) and (("InSb" or "InAs" or "PbTe") and (("SOI" or insulat\$\$) adj substrate))) not (("SOI" adj transistor) and bandgap)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 17:59
-	7	((((channel and (narrow or low) adj (bandgap or (band adj gap)))) and (("InSb" or "InAs" or "PbTe") and (("SOI" or insulat\$\$) adj substrate))) not (("SOI" adj transistor) and bandgap)) and ((source and drain) with (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 18:34

-	19	(narrow or low) adj (bandgap or (band adj gap)) adj channel	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 18:35
-	18	((narrow or low) adj (bandgap or (band adj gap)) adj channel) and (substrate and source and drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 18:35
-	10	((narrow or low) adj (bandgap or (band adj gap)) adj channel) and (substrate and source and drain)) and ("SOI" or (insulat\$4 adj substrate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 18:36
-	10	((narrow or low) adj (bandgap or (band adj gap)) adj channel) and (substrate and source and drain)) and ("SOI" or (insulat\$4 adj substrate))) not (((("SOI" adj transistor) and bandgap) (((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4)) and source and drain) and channel) (((channel and (narrow or low) adj (bandgap or (band adj gap)))) and (("InSb" or "InAs" or "PbTe") and ("SOI" or insulat\$4) adj substrate))) not (("SOI" adj transistor) and bandgap)) and ((source and drain) with (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:29
-	8	((narrow or low) adj (bandgap or (band adj gap)) adj channel) and (substrate and source and drain)) not (((narrow or low) adj (bandgap or (band adj gap)) adj channel) and (substrate and source and drain)) and ("SOI" or (insulat\$4 adj substrate))) not (("SOI" adj transistor) and bandgap) (((("SOI" adj transistor) and bandgap) and (dielectric or insulat\$4)) and source and drain) and channel) (((channel and (narrow or low) adj (bandgap or (band adj gap)))) and (("InSb" or "InAs" or "PbTe") and ("SOI" or insulat\$4) adj substrate))) not (("SOI" adj transistor) and bandgap)) and ((source and drain) with (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:29
-	6	(channel near (narrow or low) adj (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:37
-	35	(channel near3 (narrow or low) adj (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:37
-	54	(source or drain) near3 ((wide\$3 or high) adj (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:43
-	2	((channel near3 (narrow or low) adj (bandgap or (band adj gap)))) and ((source or drain) near3 ((wide\$3 or high) adj (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 19:39
-	13	((source or drain) near3 ((wide\$3 or high) adj (bandgap or (band adj gap)))) and ("SOI" or (insulat\$4 adj substrate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:12
-	115	("SOI" or (insulat\$4 adj substrate)) and ((band adj gap) or bandgap) with (source and drain)) and channel	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:17
-	4	((("SOI" or (insulat\$4 adj substrate)) and ((band adj gap) or bandgap) with (source and drain)) and channel) and (channel with ("InSb" or "InAs" or "PbTe"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:27

-	8	((("SOI" or (insulat\$4 adj substrate)) and ((band adj gap) or bandgap) with (source and drain)) and channel) and (channel with ((narrow or low) adj (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:46
-	3	("5198379"   "5420048"   "5427962").PN.	USPAT	2004/03/04 20:35
-	120	channel with ((low or narrow) adj (bandgap or (band adj gap)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:47
-	33	(channel with ((low or narrow) adj (bandgap or (band adj gap)))) and ((source or drain) with ((high\$3 or wide\$3) with (bandgap or (band adj gap))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:48
-	13	((channel with ((low or narrow) adj (bandgap or (band adj gap)))) and ((source or drain) with ((high\$3 or wide\$3) with (bandgap or (band adj gap)))) and (("SOI" or insulat\$4) adj substrate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/04 20:49
-	19	((narrow or low) adj (bandgap or (band adj gap))) adj channel	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 15:27
-	2	((narrow or low) adj (bandgap or (band adj gap))) adj channel) and (channel with ("InAs" or "PdTe" or "InSb"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 15:53
-	5	((narrow or low) adj (bandgap or (band adj gap))) adj channel) and ((narrow or low) adj (bandgap or (band adj gap)) adj material)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 15:27
-	14	((narrow or low) adj (bandgap or (band adj gap))) adj channel) not (((narrow or low) adj (bandgap or (band adj gap))) adj channel) and ((narrow or low) adj (bandgap or (band adj gap)) adj material)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 15:57
-	18	((("SOI" or insulat\$4) adj substrate) and ((low or narrow) adj (bandgap or (band adj gap))) near2 channel	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 16:01
-	8	((("SOI" or insulat\$4) adj substrate) and ((low or narrow) adj (bandgap or (band adj gap))) near2 channel) not (((narrow or low) adj (bandgap or (band adj gap))) adj channel)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/05 16:01
-	15	(US-6620662-\$ or US-5844261-\$ or US-5811844-\$ or US-5111255-\$ or US-6087207-\$ or US-5986291-\$ or US-5798540-\$ or US-5364816-\$ or US-6049110-\$ or US-5161235-\$ or US-6201267-\$ or US-5358878-\$ or US-5698869-\$ or US-5430310-\$ or US-5164797-\$).did.	USPAT	2004/07/16 11:05
-	62	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:15
-	62	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:16
-	0	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:17

-	48	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:17
-	35	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)) and (substrate and (dielectric or insulat\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:18
-	4	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)) and (substrate and (dielectric or insulat\$4))) and (dielectric near3 constant)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 05:47
-	13	("4603471"   "4769689"   "4835112"   "5095358"   "5134447"   "5245208"   "5250818"   "5266813"   "5268324"   "5378923"   "5426069"   "5475244"   "5553566").PN.	USPAT	2004/07/24 05:25
-	62	5698869.URPN.	USPAT	2004/07/24 05:46
-	31	((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)) and (substrate and (dielectric or insulat\$4))) not (((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)) and (substrate and (dielectric or insulat\$4))) and (dielectric near3 constant)) ("4603471"   "4769689"   "4835112"   "5095358"   "5134447"   "5245208"   "5250818"   "5266813"   "5268324"   "5378923"   "5426069"   "5475244"   "5553566").PN.))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 06:15
-	25	"5581092"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 06:15
-	22	"5581092" and (substrate and gate and source and drain and channel)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 06:16
-	2	("5581092" and (substrate and gate and source and drain and channel)) and ((band adj gap) or bandgap)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/24 06:16